

### High Performance Bipolar NPN RF Transistor

- High transducer gain of typ. 14 dB @ 25 mA,6 GHz
- Low minimum noise figure of typ. 0.85 dB @ 6GHz
- High output compression of typ. 11 dBm @ 25 mA
- Pb-free (RoHS compliant) package
- For a wide range of non-automotive applications
  - 2nd and 3rd LNA stage and mixer stage in LNB
  - 5.8 GHz analog/digital cordless phone
  - Satellite radio SDARS
  - WLAN, WIMAX, UWB



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration					Package	
BF888	RYs	1=B	2=E	3=C	4=E	-	-	SOT343

**Maximum Ratings** at  $T_A$  = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V <sub>CEO</sub>		V
<i>T</i> <sub>A</sub> = 25 °C		4.0	
<i>T</i> <sub>A</sub> = − 55 °C		3.5	
Collector-emitter voltage	V <sub>CES</sub>	13	
Collector-base voltage	V <sub>CBO</sub>	13	
Emitter-base voltage	V <sub>EBO</sub>	1.2	
Collector current	I <sub>C</sub>	30	mA
Base current	I <sub>B</sub>	3	
Total power dissipation <sup>1)</sup>	P <sub>tot</sub>	160	mW
<i>T</i> <sub>S</sub> ≤ 89 °C			
Junction temperature	TJ	150	°C
Ambient temperature	T <sub>A</sub>	-55 150	
Storage temperature	T <sub>Stg</sub>	-55 150	

 $^{1}\mathcal{T}_{S}$  is measured on the emitter lead at the soldering point to the pcb

#### **Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	R <sub>thJS</sub>	≤ 380	K/W



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Parameter	Symbol	Values			Unit
		min.	typ.	max.	]
DC Characteristics			•		
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	4	4.7	-	V
<i>I</i> <sub>C</sub> = 1 mA, <i>I</i> <sub>B</sub> = 0					
Collector-emitter cutoff current	I <sub>CES</sub>	-	1	-	nA
$V_{\rm CE}$ = 5 V, $V_{\rm BE}$ = 0					
Collector-base cutoff current	I <sub>CBO</sub>	-	1	-	
$V_{\rm CB} = 5 \text{ V}, I_{\rm E} = 0$					
Emitter-base cutoff current	I <sub>EBO</sub>	-	10	-	
$V_{\rm EB} = 0.5  \text{V},  I_{\rm C} = 0$					
DC current gain	h <sub>FE</sub>	-	250	-	-
$I_{\rm C}$ = 25 V, $V_{\rm CE}$ = 3 V, pulse measured					

# **Electrical Characteristics** at $T_A = 25^{\circ}C$ , unless otherwise specified

<sup>1</sup>For calculation of  $R_{\rm thJA}$  please refer to Application Note Thermal Resistance



Parameter	Symbol		Values		Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency	f <sub>T</sub>	-	47	-	GHz
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 3 V, $f$ = 2 GHz					
Collector-base capacitance	C <sub>cb</sub>	-	0.08	-	pF
$V_{CB}$ = 3 V, f=1 MHz, $V_{BE}$ = 0, emitter grounded					
Collector emitter capacitance	C <sub>ce</sub>	-	0.35	-	
$V_{CE}$ = 3 V, f = 1 MHz, $V_{BE}$ = 0, base grounded					
Emitter-base capacitance	C <sub>eb</sub>	-	0.45	-	
$V_{\text{EB}}$ = 0.5 V, <i>f</i> =1 MHz, $V_{\text{CB}}$ =0, collector grounded					
Noise figure	F				dB
<i>I</i> <sub>C</sub> = 8 mA, <i>V</i> <sub>CE</sub> = 3 V, <i>f</i> = 1.8 GHz, <i>Z</i> <sub>S</sub> = <i>Z</i> <sub>Sopt</sub>		-	0.5	-	
$I_{\rm C}$ = 8 mA, $V_{\rm CE}$ = 3 V, $f$ = 6 GHz, $Z_{\rm S}$ = $Z_{\rm Sopt}$		-	0.85	-	
Power gain	G <sub>ms</sub>	-	27	-	dB
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 3 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ , $Z_{\rm L}$ = $Z_{\rm Lopt}$ ,					
<i>f</i> = 1.8 GHz					
Power gain, maximum available <sup>1)</sup>	G <sub>ma</sub>	-	17	-	dB
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 3 V, $Z_{\rm S}$ = $Z_{\rm Sopt,}$ $Z_{\rm L}$ = $Z_{\rm Lopt,}$					
<i>f</i> = 6 GHz					
Transducer gain	S <sub>21e</sub>   <sup>2</sup>				dB
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 3 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 $\Omega$ ,					
<i>f</i> = 1.8 GHz		-	24.5	-	
<i>f</i> = 6 GHz		-	14	-	
Third order intercept point at output <sup>2)</sup>	IP <sub>3</sub>	-	25	-	dBm
V <sub>CE</sub> = 3 V, <i>I</i> <sub>C</sub> = 25 mA, <i>f</i> = 1.8 GHz,					
$Z_{\rm S} = Z_{\rm L} = 50 \ \Omega$					
1dB Compression point	P <sub>-1dB</sub>	-	11	-	1
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 3 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 $\Omega$ ,					
<i>f</i> = 1.8 GHz					

Electrical Characteristics a	at T.	= 25°C	unlage	otherwise	specified
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 ${}^{1}G_{\text{ma}} = |S_{21e} / S_{12e}| \ (k - (k^{2} - 1)^{1/2})$ 

<sup>2</sup>IP3 value depends on termination of all intermodulation frequency components.

Termination used for this measurement is 50  $\Omega$  from 0.1 MHz to 6 GHz





## Foot Print



## Marking Layout (Example)



# Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel





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